

FC804

Silicon Schottky Barrier Diode

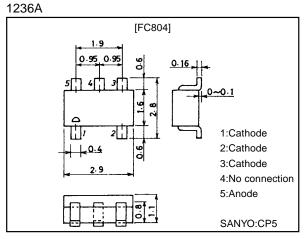
30V, 200mA Rectifier

Features

- \cdot Low forward voltage (V_F max=0.55V).
- \cdot Fast reverse recorvery time (trr max=10ns) .
- Composite type with 2 diodes contained in the CP package currently in use, improving the mounting efficiency greatly.
- The FC804 is formed with two chips, each being equivalent to the SB02–03C, placed in one package.

Package Dimensions

unit:mm



Specifications

Absolute Maximum Ratings at Ta = 25°C

| Parameter | Symbol | Conditions | Ratings | Unit |
|---|------------------|--------------------------|-------------|------|
| Repetitive Peak Reverse Voltage | V _{RRM} | | 30 | V |
| 2Nonrepetitive Peak Reverse Surge Voltage | VRSM | | 35 | V |
| Average Output Current | I _O | | 200 | mA |
| Surge Forward Current | IFSM | 50MHz sine wave, 1 cycle | 2 | A |
| Junction Temperature | Tj | | -55 to +125 | °C |
| Storage Temperature | Tstg | | -55 to +125 | °C |

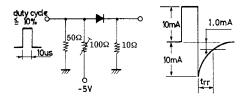
Electrical Characteristics at Ta = 25°C

| Parameter | Symbol | Conditions | Ratings | | | Unit |
|--------------------------|----------------|---|---------|-----|------|------|
| | | | min | typ | max | |
| Reverse Voltage | VR | I _R =50µA | 30 | | | V |
| Forward Voltage | ٧ _F | I _F =200mA | | | 0.55 | V |
| Reverse Current | I _R | V _R =15V | | | 15 | μΑ |
| Interteminal Capacitance | С | V _R =10V, f=1MHz | | 6.3 | | pF |
| Reverse Recovery Time | trr | I _F =I _R = (-) 10mA, See specified Test Circuit | | | 10 | ns |

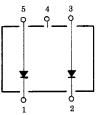
Note) The specifications shown above are for each individual diode.

· Marking:804

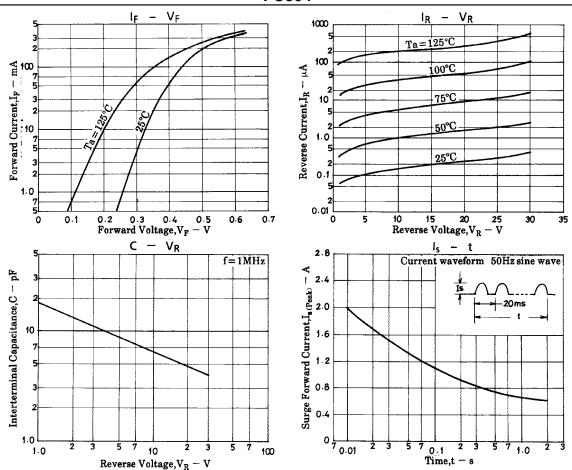
trr Test Circuit







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